

**AMENDMENTS TO THE SPECIFICATION**

After the title of the invention and before the heading "Field of the Invention" on page 1 of the specification, please add the following paragraph:

This application is a division of U.S. patent application Serial No. 10/305,075, filed November 27, 2002.

Please amend the following paragraphs of the specification as shown:

[0006] Storage capacitors may also provide useful results when electrically connected to other light sensitive and/or electrical elements of the pixel sensor cell, such as transistor gates or floating diffusion regions, for example, to affect the operation and characteristics of such various light sensitive and/or electrical elements. Capacitors connected to such various light sensitive and/or electrical elements of the pixel sensor cell help amplify the signal of an imager transistor, increase the storage capacitance of a photosite, or provide a low noise decoupling capacitor. Such storage capacitors are described in co-pending U.S. patent application Serial No. 10/303,896, filed November 26, 2002, by Howard E. Rhodes and Jeff McKee, entitled "CMOS IMAGER PIXEL DESIGNS" (~~attorney docket number M4065.0570~~), the entire disclosure of which is incorporated herein by reference. While the use of storage capacitors at various locations within a pixel improve pixel operation, those capacitors have the same capacitance value for each pixel color and are not optimized for the photon to charge conversion characteristics of each color pixel.

[0023] Methods of manufacturing the pixels disclosed herein are taught in related U.S. Patent Application Serial No. 10/303,896, filed November 26, 2002 (~~attorney docket number M4065.0570~~), in the names of Howard E. Rhodes and Jeff McKee, and entitled "CMOS IMAGER PIXEL DESIGNS," the disclosure of which ~~application~~ is incorporated herein by reference.